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(54) **OLED DEVICE AND METHOD FOR MANUFACTURING SAME, AND OLED DISPLAY PANEL**

(57) An organic light-emitting diode (OLED), a manufacturing method thereof and an OLED display panel. The OLED includes a substrate (100), an anode (1) and a cathode (2) disposed on the substrate (100), a hole transport layer (HTL) (5) and an electron transport layer (ETL) (6) disposed between the anode (1) and the cathode (2), and at least two emitting layers (EMLs) disposed between the HTL (5) and the ETL (6); the at least two EMLs emit white light; and the OLED further includes an electron blocking layer (EBL) (7) disposed between the ETL (6) and the at least two EMLs. The color stability of the OLED is improved.

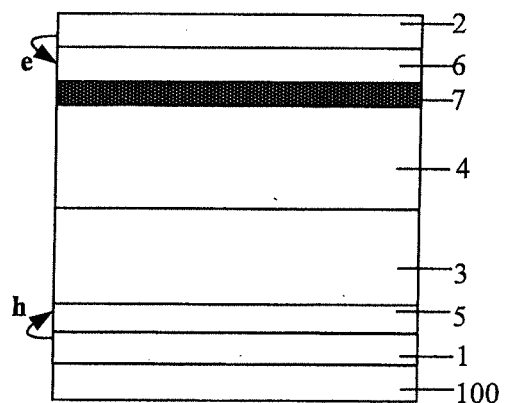


FIG. 3

Description

TECHNICAL FIELD

[0001] Embodiments of the present disclosure relate to an organic light-emitting diode (OLED), a manufacturing method thereof and an OLED display panel.

BACKGROUND

[0002] Organic light-emitting diode (OLED) is an organic thin film electroluminescent device and has the advantages of simple manufacturing process, low cost, capability of easily forming a flexible structure, wide viewing angle, etc. Therefore, display technology utilizing OLEDs has become an important display technology.

SUMMARY

[0003] Embodiments of the present disclosure provide an organic light-emitting diode (OLED), comprising a substrate, an anode and a cathode disposed on the substrate, a hole transport layer (HTL) and an electron transport layer (ETL) disposed between the anode and the cathode, and at least two emitting layers (EMLs) disposed between the HTL and the ETL, wherein the at least two EMLs emit white light; and the OLED further comprises an electron blocking layer (EBL) disposed between the ETL and the at least two EMLs.

[0004] In an embodiment of the present disclosure, for example, in the OLED, wherein a material of the EBL comprises 9,9-(1,3-Phenylene)bis-9H-carbazole (mCP).

[0005] In an embodiment of the present disclosure, for example, in the OLED, a thickness of the EBL is from 5 nm to 15 nm.

[0006] In an embodiment of the present disclosure, for example, in the OLED, the at least two EMLs comprise a red emitting layer (EML) and a blue emitting layer (EML); the red EML is arranged closer to the EBL as compared to the blue EML; and the blue EML is arranged closer to the HTL as compared to the red EML.

[0007] In an embodiment of the present disclosure, for example, in the OLED, a material of the EBL comprises mCP; and a host material of the blue EML comprises mCP.

[0008] In an embodiment of the present disclosure, for example, in the OLED, the at least two EMLs further comprise a green EML; and the green EML is disposed between the red EML and the blue EML.

[0009] In an embodiment of the present disclosure, for example, the OLED further comprising a buffer layer disposed on a surface of the cathode facing the ETL; and an energy level of the buffer layer is between an energy level of the cathode and an energy level of the ETL.

[0010] Embodiments of the present disclosure further provide an OLED display panel, comprising one of the above described OLED.

[0011] Embodiments of the present disclosure further

provide a method for manufacturing an OLED, comprising: forming an anode through a patterning process; and forming a hole transport layer (HTL), at least two emitting layers (EMLs), an electron transport layer (ETL) and a cathode on the anode sequentially through an evaporation process, wherein the at least two EMLs emit white light; and the method further comprises: forming an electron blocking layer (EBL) between the at least two EMLs and the ETL.

[0012] In an embodiment of the present disclosure, for example, in the method, the forming the at least two emitting layers (EMLs) comprises: forming a red emitting layer (EML) and a blue emitting layer (EML), in which the red EML is closer to the EBL as compared to the blue EML; the blue EML is closer to the HTL as compared to the red EML; a host material of the blue EML comprises mCP; and the forming the EBL comprises: forming the EBL with mCP.

[0013] In an embodiment of the present disclosure, for example, in the method, a thickness of the EBL is from 5 nm to 15 nm.

BRIEF DESCRIPTION OF THE DRAWINGS

[0014] In order to clearly illustrate the technical solution of the embodiments of the disclosure, the drawings of the embodiments will be briefly described in the following, it is obvious that the described drawings are only related to some embodiments of the disclosure and thus are not limitative of the disclosure.

FIG. 1 is a schematic structural view of a conventional OLED;

FIG. 2 is a schematic diagram illustrating a transformation of a chromaticity coordinate of a conventional OLED when the driving voltage is from 7 V to 21 V; FIG. 3 is a schematic structural view of an OLED provided by an embodiment of the present disclosure;

FIG. 4 is a schematic structural view of an OLED provided by another embodiment of the present disclosure;

FIG. 5 is a schematic structural view of an OLED provided by another embodiment of the present disclosure;

FIG. 6 is a schematic diagram illustrating a transformation of a chromaticity coordinate of an OLED provided by an embodiment of the present disclosure when the driving voltage is from 7 V to 21 V;

FIG. 7 is a schematic structural view of an OLED provided by still another embodiment of the present disclosure; and

FIG. 8 is a flow diagram of a method for manufacturing an OLED provided by an embodiment of the present disclosure.

[0015] Reference numerals of the accompanying drawings: 100 - substrate; 1 - anode; 2 - cathode; 3 - first

EML; 4 - second EML; 5 - HTL; 6 - ETL; 7 - EBL; 8 - HIL; 9- EIL; 10 - third EML; 11 - buffer layer.

DETAILED DESCRIPTION

[0016] In order to make objects, technical details and advantages of the embodiments of the disclosure apparent, the technical solutions of the embodiment will be described in a clearly and fully understandable way in connection with the drawings related to the embodiments of the disclosure. It is obvious that the described embodiments are just a part but not all of the embodiments of the disclosure. Based on the described embodiments herein, those skilled in the art can obtain other embodiment(s), without any inventive work, which should be within the scope of the disclosure.

[0017] Unless otherwise defined, all the technical and scientific terms used herein have the same meanings as commonly understood by one of ordinary skill in the art to which the present disclosure belongs. The terms "first," "second," etc., which are used in the description and the claims of the present application for disclosure, are not intended to indicate any sequence, amount or importance, but distinguish various components. Also, the terms such as "a," "an," etc., are not intended to limit the amount, but indicate the existence of at least one.

[0018] As shown in FIG. 1, a conventional white-light OLED comprises: a substrate 100, an anode 1 and a cathode 2 disposed on the substrate 100, and a first emitting layer (EML) 3 and a second emitting layer (EML) 4 disposed between the anode 1 and the cathode 2. The working principle of the conventional white-light OLED is that: holes injected from the anode 1 and electrons injected from the cathode 2 are recombined in the emitting layers (EMLs) to form excitons; the excitons excite luminescent molecules; and the excited luminescent molecules are subjected to radiative relaxation to emit visible light.

[0019] However, the researchers found that: the hole mobility is greater than the electron mobility (differ by three orders of magnitude). When a driving voltage applied to the OLED is increased, both the hole mobility and the electron mobility are increased, and the growth rate of the electron mobility is higher than the growth rate of the hole mobility, so the difference between the hole mobility and the electron mobility can be reduced. For instance, when an applied voltage is small, the electron mobility is low, so a number of electrons transferred into the second EML 4 close to the cathode 2 is greater than a number of electrons transferred into the first EML 3 close to the anode 1. Thus, the number of excitons in the second EML 4 is greater than the number of excitons in the first EML 3, so that the second EML 4 can receive more energy and have higher luminous intensity, and hence the luminous color of the OLED can be biased towards the color of the second EML 4. Along with the increase of the driving voltage, the growth rate of the electron mobility is higher than the growth rate of the hole

mobility, so the difference between the hole mobility and the electron mobility can be further reduced. Moreover, due to the increase of the electron mobility, the number of electrons transferred into the first EML 3 is increased, so the number of excitons in the first EML 3 is also correspondingly increased. Thus, the first EML 3 receives more energy and has higher luminous intensity, so that the luminous intensity of the first EML 3 and the second EML 4 tend to be consistent.

[0020] Therefore, in a conventional white-light OLED, when a voltage applied to the OLED changes, the luminous color of the OLED is instable, and the chromaticity coordinate drift is severe. For instance, FIG. 2 shows an International Commission on Illumination (CIE) 1931 chromaticity coordinate system, when a driving voltage changes from 7V to 21V, a change of the chromaticity coordinate of the OLED is large, and the luminous color changes from red to pink and then to white, so the color stability is poor.

[0021] The embodiment of the present disclosure provides an OLED. As illustrated in FIGS. 3-5, the OLED comprises a substrate 100, an anode 1 and a cathode 2 disposed on the substrate 100, a HTL 5 and an ETL 6 disposed between the anode 1 and the cathode 2, and at least two EMLs (3, 4, 10) disposed between the HTL 5 and the ETL 6, wherein the at least two EMLs (3, 4, 10) emit white light. Moreover, the OLED further comprises an EBL 7 disposed between the ETL 6 and the at least two EMLs (3, 4, 10).

[0022] The embodiment of the present disclosure obtains stable luminous color by the arrangement of the EBL 7. When a low voltage is applied, the increase of the electron mobility in the embodiment of the present disclosure is inhibited, so the number of electrons transferred to the EMLs tends to be identical, and hence the number of excitons in the EMLs tends to be identical. Thus, the luminous intensity of the EMLs also tends to be identical, so the OLED emits white light. Along with the increase of the applied voltage, although the growth rate of the electron mobility is higher than the growth rate of the hole mobility, due to the blocking function of the EBL 7 on electron transfer, the number of the electrons transferred to the EMLs still tends to be identical. Thus, the luminous intensity of the EMLs tends to be identical, so the OLED still emits white light.

[0023] The HTL 5 is made from hole transport materials. The hole transport materials may be triarylamine compounds, biphenyl diamine derivatives or cross-linked diamine biphenyl, for instance, may be N,N'-Diphenyl-N,N'-bis(a-naphthyl)-1,1'-biphenyl-4,4'-diamine (NPB), 4,4',4"-Tris(9-carbazoyl)triphenylamine (TCTA), 4,4',4"-Tris(N-3-methylphenyl-N-phenylamino) triphenylamine (m-MTDATA), etc.

[0024] The ETL 6 is made from electron transport materials. The electron transport materials may be metal chelates, azole compounds, phenanthroline derivatives or the like, for instance, may be: tris(8-hydroxyquinoline)aluminum (AlQ₃), 4,7-diphenyl-1,10-orthophenan-

throline (BPhen), 1,3,5-tris[(3-pyridyl)-3-phenyl]benzene (TmPyPB), 2,2'-(1,3-phenyl)bis[5-(4-tert-butylphenyl)-1,3,4-oxadiazole] (OXD-7), etc.

[0025] It should be noted that: firstly, the specific number of the at least two EMLs is not limited, as long as white light can be emitted. The structure as shown in FIGS. 3 and 5 includes two EMLs, namely the first EML 3 and the second EML 4; and the structure as shown in FIG. 4 includes three EMLs, namely the first EML 3, the second EML 4 and a third EML 10.

[0026] A material of each EML in the at least two EMLs may be a hole transport material or an electron transport material.

[0027] For instance, the EML close to the anode 1 is made from the hole transport materials, and the EML close to the cathode 2 is made from the electron transport materials. As shown in FIG. 3, for instance, a material of the first EML 3 is a hole transport material, and a material of the second EML 4 is an electron transport material.

[0028] Secondly, a material of the EBL 7 is not specifically limited, as long as the EBL can have the function of blocking electrons. For instance, a material of the EBL may be a hole transport material.

[0029] Thirdly, as shown in FIG. 5, in order to increase the injection efficiency of the electrons and the holes, an HIL 8 may be further disposed between the anode 1 and the first EML 3, and an EIL 9 may be further disposed between the cathode 2 and the second EML 4.

[0030] The embodiment of the present disclosure provides an OLED. As the EBL 7 is disposed between the at least two EMLs and the ETL 6, a change of the electron mobility may be inhibited when the driving voltage applied to the OLED changes, so that the number of electrons transferred to the EMLs tends to be identical, and hence the number of excitons in the EMLs tends to be identical. Thus, the luminous intensity of the EMLs tends to be identical, so that the luminous color of the OLED can be stable and the chromaticity coordinate drift can be reduced.

[0031] Considering that 9,9-(1,3-Phenylene)bis-9H-carbazole (mCP) materials are good hole transport materials, electron transfer blocking effects can be well achieved using mCP. Therefore, a material of the EBL 7, for instance, may comprise mCP.

[0032] As shown in FIG. 6 which is a CIE1931 chromaticity coordinate system, in the case that a material of the EBL 7 comprises mCP, when the driving voltage gradually changes from 7 V to 21 V, as shown by dotted lines in FIG. 6 (triangles in the dotted lines refer to the chromaticity coordinates of the luminous color of the OLED under different driving voltages), a change of the chromaticity coordinate of the OLED is small, and good color stability is obtained.

[0033] For instance, a thickness of the EBL 7 is from 5 nm to 15 nm.

[0034] When the thickness of the EBL 7 is set from 5 nm to 15 nm, electron transfer can be well blocked by the EBL. For example, when the thickness of the EBL 7

is 10 nm, the electron blocking effect is good, and the entire OLED is light and thin.

[0035] For instance, the at least two EMLs comprise a red EML and a blue EML; the red EML is arranged closer to the EBL 7 as compared to the blue EML; and the blue EML is arranged closer to the HTL 5 as compared to the red EML.

[0036] That is to say, as shown in FIG. 3, the first EML 3 is a blue EML, and the second EML 4 is a red EML.

[0037] A material of the blue EML, for instance, may adopt a host-guest doping system, in which host materials may adopt iridium (Ir) complexes such as bis(4,6-difluorophenylpyridinato-N,C2)picolinatoiridium (FIrpic), and guest materials may adopt 4,4'-Bis(N-carbazolyl)-1,1'-biphenyl (CBP), 1,3-bis(triphenylsilyl)benzene (UGH3), mCP, etc. For instance, the materials of the blue EML are CBP: 9% FIrpic.

[0038] A material of the red EML, for instance, may adopt a host-guest doping system, in which a guest material may adopt Ir complexes such as bis(2-methyldibenzo[F,H]quinoxaline)(acetylacetonate)iridium(III) (Ir(MDQ)2acac), and a host material may adopt CBP, etc. For instance, the materials of the red EML are CBP: 2% Ir(MDQ)2acac.

[0039] In the present embodiment of the disclosure, as red and blue are two complementary colors, the superimposition of the blue EML and the red EML allows the OLED to emit white light. As the blue EML comprises hole transport materials, an energy level difference between the EML and the anode 1 can be reduced by disposing the blue EML close to the HTL 5 and hence the luminescent properties of the EML can be improved; and as the red EML comprises electron transport materials, the energy level difference between the EML and the cathode 2 can be reduced by disposing the red EML close to the ETL 6 and hence the luminescent properties of the EML can be improved.

[0040] For instance, a material of the EBL 7 comprises mCP; and a host material of the blue EML comprises mCP.

[0041] In the present embodiment of the disclosure, a host material of the EBL 7 and the blue EML adopt same materials, as a result, a replacement frequency of different materials in the evaporation process is reduced, and hence the manufacturing process is simplified and the production efficiency is improved.

[0042] For instance, the at least two EMLs comprise a red EML, a blue EML and a green EML; and the green EML is disposed between the red EML and the blue EML.

[0043] That is to say, as shown in FIG. 4, the first EML 3 is a blue EML; the second EML 4 is a red EML; and the third EML 10 is a green EML.

[0044] Compared with the OLED only comprising a red EML and a blue EML, the OLED further comprising a green EML has higher color rendering index.

[0045] On this basis, considering that the energy level difference between the cathode 2 and the ETL 6 is large and the electron transport efficiency is low, for instance,

as shown in FIG. 7, the OLED further comprises a buffer layer 11 disposed on a surface of the cathode 2 facing the ETL 6. The buffer layer 11 is configured to match the energy level of the cathode 2 and the ETL 6.

[0046] The materials of the buffer layer 11 are not specifically limited, as long as the buffer layer can achieve the energy level buffering between the cathode 2 and the ETL 6. For instance, a material of the buffer layer 11 may be LiF, etc.

[0047] An embodiment of the present disclosure provides an OLED display panel, which comprises the foregoing OLED.

[0048] In the OLED display panel provided by the embodiment of the present disclosure, as the EBL 7 is disposed between the at least two EMLs and the ETL 6 of the OLED, when a driving voltage applied to the OLED changes, the change of the electron mobility can be inhibited, so the number of electrons transferred to the EMLs tends to be identical, and hence the number of excitons in the EMLs tends to be identical. Thus, the luminous intensity of the EMLs tends to be identical, so that the luminous color of the OLED is stabilized and the chromaticity coordinate drift is reduced, and hence the display effect of the OLED display panel can be improved.

[0049] The embodiment of the present disclosure provides a method for manufacturing an OLED. As illustrated in FIG. 8, the method comprises:

S01: as shown in FIGS. 3-4, forming an anode 1 on a substrate 100 through a patterning process.

[0050] The substrate 100, for instance, may be transparent glass. A material of the anode 1, for instance, may be indium tin oxide (ITO).

[0051] Considering that a surface state of the anode 1 directly affects hole injection, affects the interface electronic state of organic layers, and affects the film forming property of organic materials, the surface treatment of the substrate 100 is very important. On this basis, before the anode 1 is formed, the substrate 100 must be subjected to surface treatment, for instance, including: placing the cleaned substrate 100 into clean water, anhydrous ethanol, acetone, anhydrous ethanol, acetone and isopropyl alcohol respectively, adopting an ultrasonic wave cleaner for treatment, and placing the substrate into anhydrous ethanol for storage after the completion of cleaning.

[0052] S02: as shown in FIGS. 3-4, forming a HTL 5 on the anode 1 through an evaporation process.

[0053] A hole transport material may comprise triarylamine compounds, biphenyl diamine derivatives or cross-linked diamine biphenyl, for instance, may be NPB, TCTA, m-MTDATA, etc.

[0054] S03: forming at least two EMLs on the HTL 5 through an evaporation process.

[0055] As shown in FIG. 3, the at least two EMLs comprise a first EML 3 and a second EML 4. Or as shown in FIG. 4, the at least two EMLs comprise a first EML 3, a second EML 4 and a third EML 10.

[0056] The first EML 3 may be a blue EML; the second

EML 4 may be a red EML; and the third EML 10 may be a green EML.

[0057] S04: forming an EBL 7 on the at least two EMLs through an evaporation process.

5 [0058] A material of the EBL 7 is not specifically limited, as long as an electron blocking effect can be obtained through the EBL. For instance, a material of the EBL may comprise a hole transport material.

10 [0059] S05: forming an ETL 6 on the EBL 7 through an evaporation process.

[0060] The ETL 6 is made from electron transport materials. The electron transport materials may comprise metal chelates, azole compounds, phenanthroline derivatives or the like, for instance, may be: AlQ₃, BPhen, TmPyPB, OXD-7.

15 [0061] S06: forming a cathode 2 on the ETL 6 through an evaporation process.

[0062] A material of the cathode 2 may comprise metallic materials such as aluminum (Al), aurum (Au), argentums (Ag) and magnesium (Mg)-Ag alloy.

20 [0063] In the embodiment of the present disclosure, the evaporation process, for instance, may include: evaporating target materials into atoms or molecules by electric heating. The atoms and the molecules will be disengaged from the materials and move up due to thermal motion, make contact with the substrate 100 in the moving process, and are accumulated and condensed on the substrate 100 to form layers. The processes of forming the layers by high-temperature evaporation are all performed in an environment with a pressure less than 4×10^{-4} Pa.

25 [0064] The embodiment of the present disclosure provides a method for manufacturing an OLED. As the EBL 7 is formed between the at least two EMLs and the ETL 6, the change of the electron mobility may be inhibited when the driving voltage applied to the OLED changes, so that the number of electrons transferred to the EMLs tends to be identical, and hence the number of excitons in the EMLs tends to be identical. Thus, the luminous intensity of the EMLs tends to be identical, so that the luminous color of the OLED can be stabilized and the chromaticity coordinate drift is reduced.

30 [0065] For instance, the forming the at least two EMLs comprises: forming a red EML and a blue EML, in which the red EML is formed closer to the EBL 7 as compared to the blue EML; the blue EML is formed closer to the HTL 5 as compared to the red EML; and a host material of the blue EML may comprise mCP. On this basis, the forming the EBL 7 includes: forming the EBL 7 with mCP.

35 [0066] In the present embodiment of the present disclosure, a host material of the EBL 7 and the blue EML adopt same materials, as a result, a replacement frequency of different materials in the evaporation process is reduced, and hence the manufacturing process is simplified and the production efficiency is improved.

40 [0067] For instance, the method further comprises forming a green EML. The green EML is disposed between the red EML and the blue EML.

[0068] For instance, a thickness of the EBL 7 is from 5 nm to 15 nm.

[0069] When the thickness of the EBL 7 is from 5 nm to 15 nm, electron transfer can be well blocked by the EBL. Particularly when the thickness of the EBL 7 is 10 nm, the electron blocking effect is good, and the entire OLED is light and thin.

[0070] What are described above is related to the illustrative embodiments of the disclosure only and not limitative to the scope of the disclosure; the scopes of the disclosure are defined by the accompanying claims.

[0071] The present application claims the priority of the Chinese Patent Application No.201610279225.4 filed on April 28, 2016, which is incorporated herein by reference as part of the disclosure of the present application.

Claims

1. An organic light-emitting diode (OLED), comprising a substrate, an anode and a cathode disposed on the substrate, a hole transport layer (HTL) and an electron transport layer (ETL) disposed between the anode and the cathode, and at least two emitting layers (EMLs) disposed between the HTL and the ETL, wherein the at least two EMLs emit white light; and the OLED further comprises an electron blocking layer (EBL) disposed between the ETL and the at least two EMLs.
2. The OLED according to claim 1, wherein a material of the EBL comprises 9,9-(1,3-Phenylene)bis-9H-carbazole (mCP).
3. The OLED according to claim 1 or 2, wherein a thickness of the EBL is from 5 nm to 15 nm.
4. The OLED according to any one of claims 1 to 3, wherein the at least two EMLs comprise a red emitting layer (EML) and a blue emitting layer (EML); the red EML is arranged closer to the EBL as compared to the blue EML; and the blue EML is arranged closer to the HTL as compared to the red EML.
5. The OLED according to any one of claims 1 to 4, wherein a material of the EBL comprises mCP; and a host material of the blue EML comprises mCP.
6. The OLED according to claim 4, wherein the at least two EMLs further comprise a green EML; and the green EML is disposed between the red EML and the blue EML.
7. The OLED according to claim 1, further comprising a buffer layer disposed on a surface of the cathode facing the ETL; and an energy level of the buffer layer is between an energy level of the cathode and an energy level of the ETL.
8. An OLED display panel, comprising the OLED according to any one of claims 1 to 7.
9. A method for manufacturing an OLED, comprising: forming an anode through a patterning process; and forming a hole transport layer (HTL), at least two emitting layers (EMLs), an electron transport layer (ETL) and a cathode on the anode sequentially through an evaporation process, wherein the at least two EMLs emit white light; and the method further comprises: forming an electron blocking layer (EBL) between the at least two EMLs and the ETL.
10. The manufacturing method according to claim 9, wherein forming of the at least two emitting layers (EMLs) comprises: forming a red emitting layer (EML) and a blue emitting layer (EML), in which the red EML is closer to the EBL as compared to the blue EML; the blue EML is closer to the HTL as compared to the red EML; a host material of the blue EML comprises mCP; and forming of the EBL comprises: forming the EBL with mCP.
11. The manufacturing method according to claim 10, wherein a thickness of the EBL is from 5 nm to 15 nm.

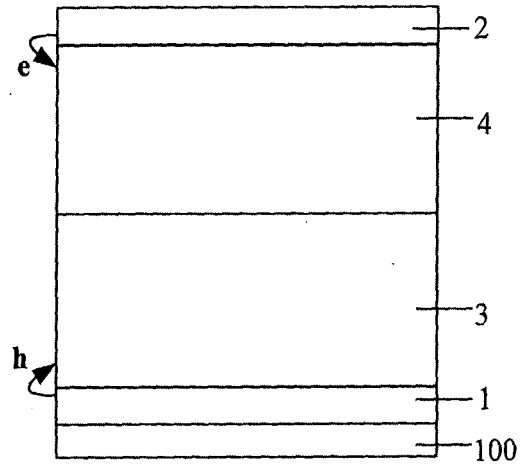


FIG. 1

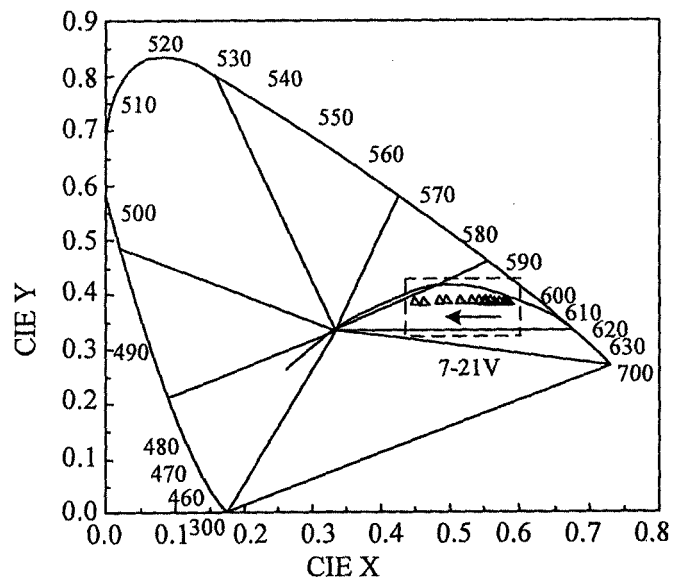


FIG. 2

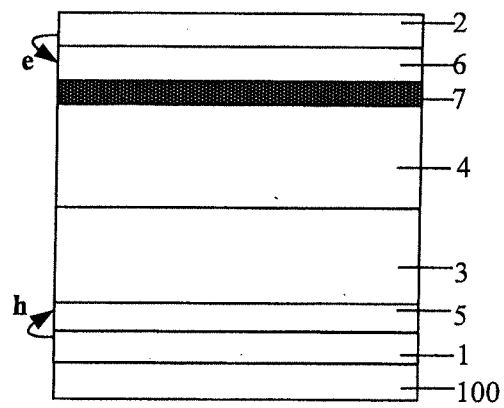


FIG. 3

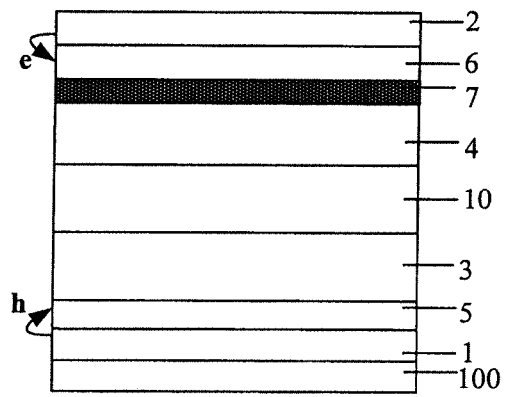


FIG. 4

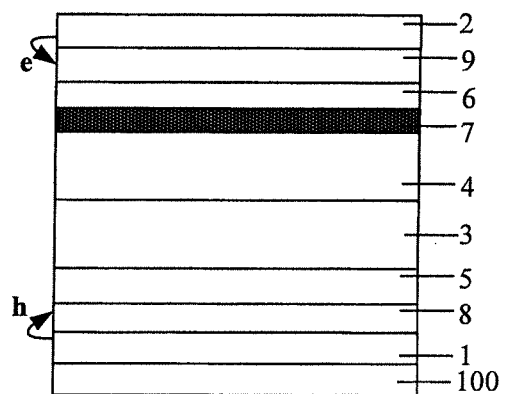


FIG. 5

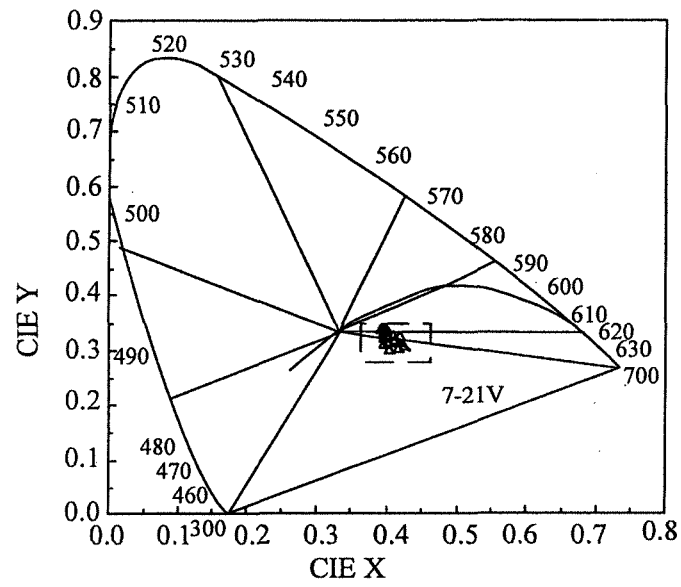


FIG. 6

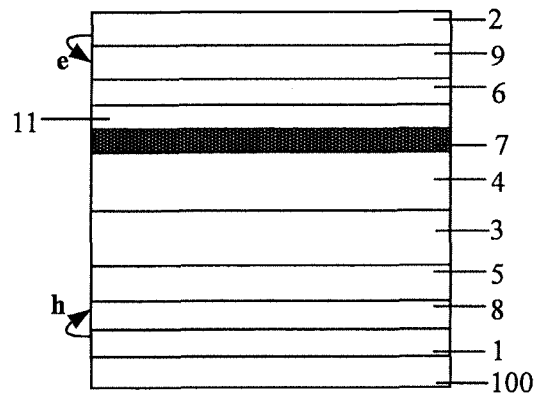


FIG. 7

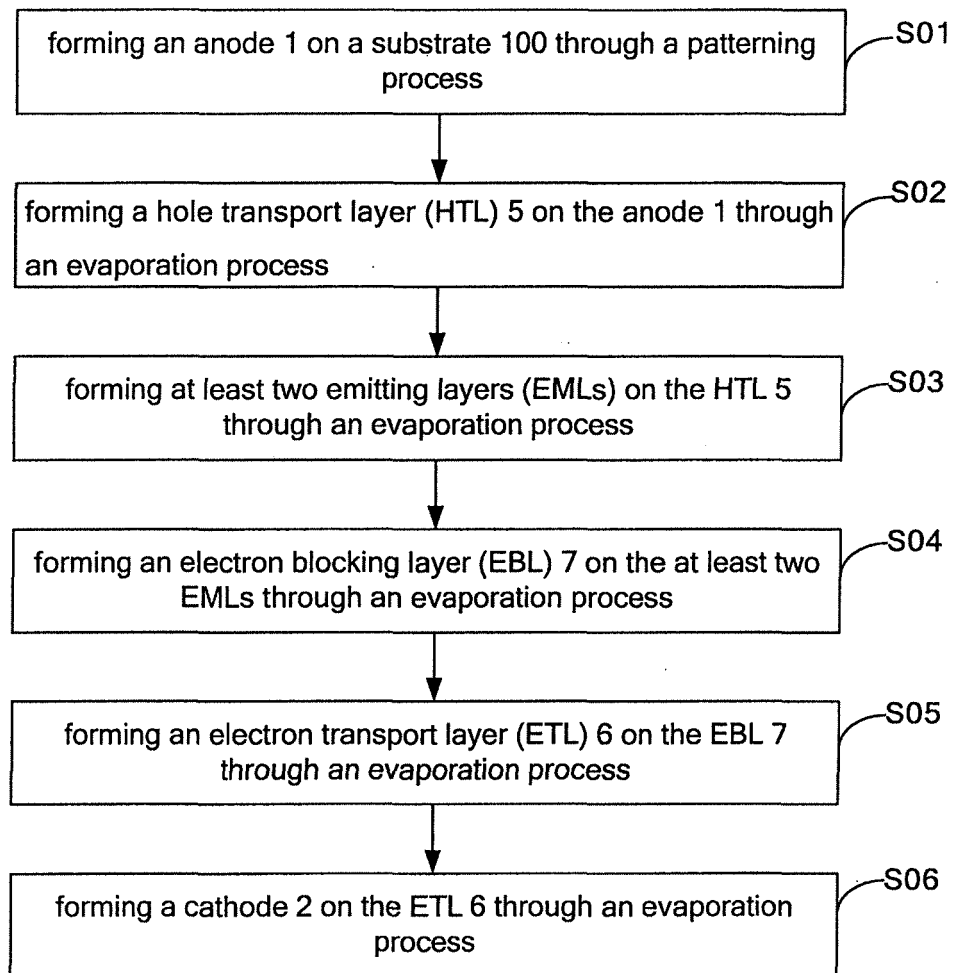


FIG. 8

INTERNATIONAL SEARCH REPORT

International application No.

PCT/CN2017/071725

A. CLASSIFICATION OF SUBJECT MATTER

H01L 51/50 (2006.01) i; H01L 51/56 (2006.01) i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CNABS; USTXT; EPTXT; CNTXT; WOTXT; SIPOABS; DWPI: organic light-emitting, electron transport, electron blocking, hole transport, light-emitting layer, emission layer, double, multilayer, organic, electroluminescen+, electron, transport+, block+, hole, emit+, emission, two, second, several

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	CN 103329621 A (IDEMITSU KOSAN CO., LTD.), 25 September 2013 (25.09.2013), description, paragraphs [0069]-[0073], [0107], [0108], [0171]-[0207], [0215]-[0230] and [0415]-[0425]	1, 3-4, 6-9
Y	CN 103329621 A (IDEMITSU KOSAN CO., LTD.), 25 September 2013 (25.09.2013), description, paragraphs [0069]-[0073], [0107], [0108], [0171]-[0207], [0215]-[0230] and [0415]-[0425]	2, 5, 10, 11
Y	CN 101180304 A (UNIVERSAL DISPLAY CORPORATION), 14 May 2008 (14.05.2008), description, page 64, line 15 to page 65, line 3, and figure 51	2, 5, 10, 11
Y	CN 102945928 A (JILIN UNIVERSITY), 27 February 2013 (27.02.2013), description, paragraph [0019]	5, 10, 11
A	US 2009026929 A1 (SONG, J.B. et al.), 29 January 2009 (29.01.2009), the whole document	1-11
PX	CN 105895819 A (BOE TECHNOLOGY GROUP CO., LTD. et al.), 24 August 2016 (24.08.2016), description, paragraphs [0006]-[0019]	1-11

☐ Further documents are listed in the continuation of Box C.
☒ See patent family annex.

* Special categories of cited documents:	"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"A" document defining the general state of the art which is not considered to be of particular relevance	
"E" earlier application or patent but published on or after the international filing date	"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O" document referring to an oral disclosure, use, exhibition or other means	
"P" document published prior to the international filing date but later than the priority date claimed	"&" document member of the same patent family

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INTERNATIONAL SEARCH REPORT
 Information on patent family members

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Patent Documents referred in the Report	Publication Date	Patent Family	Publication Date
CN 103329621 A	25 September 2013	US 8847218 B2	30 September 2014
		EP 2667688 A1	27 November 2013
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REFERENCES CITED IN THE DESCRIPTION

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专利名称(译)	OLED装置及其制造方法以及OLED显示面板		
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优先权	201610279225.4 2016-04-28 CN		
其他公开文献	EP3451401A1		
外部链接	Espacenet		

摘要(译)

有机发光二极管 (OLED) , 其制造方法和OLED显示面板。 OLED包括基板 (100) , 设置在基板 (100) 上的阳极 (1) 和阴极 (2) , 设置的空穴传输层 (HTL) (5) 和电子传输层 (ETL) (6) 。 在阳极 (1) 和阴极 (2) 之间 , 以及至少两个位于HTL (5) 和ETL (6) 之间的发射层 (EML) ; 至少两个EML发出白光 ; OLED还包括设置在ETL (6) 和至少两个EML之间的电子阻挡层 (EBL) (7) 。 OLED的颜色稳定性得到改善。